

Amendments to the Claims

The listing of claims will replace all prior versions, and listings of claims in the application.

1. (cancelled)
2. (currently amended) A capacitor for an integrated circuit comprising:
 - a first MOS-on-NWELL (Metal Oxide Semiconductor-on-N-doped well) device formed on a substrate and having a first pickup terminal and a first gate;
 - a second MOS-on-NWELL device formed on the substrate and having a second pickup terminal and a second gate,
 - wherein the first gate is connected to the second pickup terminal, and
 - wherein the second gate is connected to the first pickup terminal;
 - a first PMOS (P-channel Metal Oxide Semiconductor ~~Field-Effect~~) transistor formed on the substrate and having its source and drain terminals connected together;
 - and
 - a second PMOS transistor formed on the substrate and having its source and drain terminals connected together,
 - wherein a gate of the first PMOS transistor is connected to the source and drain terminals of the second PMOS transistor,
 - wherein a gate of the second PMOS transistor is connected to the source and drain terminals of the first PMOS transistor,
 - wherein the first gate, the second pickup terminal, the gate of the first PMOS transistor and the source and drain terminals of the second PMOS transistor are connected to a first common terminal, and
 - wherein the second gate, the first pickup terminal, the gate of the second PMOS transistor and the source and drain terminals of the first PMOS transistor are connected to a second common terminal.

3. (cancelled)
4. (cancelled)
5. (cancelled)
6. (cancelled)
7. (currently amended) A capacitor for an integrated circuit comprising:
 - a first MOS-on-PWELL (Metal Oxide Semiconductor-on-P-doped well) device formed on a substrate and having a first pickup terminal and a first gate;
 - a second MOS-on-PWELL device formed on the substrate and having a second pickup terminal and a second gate,
 - wherein the first gate is connected to the second pickup terminal, and
 - wherein the second gate is connected to the first pickup terminal;
 - a first NMOS (N-channel Metal Oxide Semiconductor ~~Field-Effect~~) transistor formed on the substrate and having its source and drain terminals connected together; and
 - a second NMOS transistor formed on the substrate and having its source and drain terminals connected together,
 - wherein a gate of the first NMOS transistor is connected to the source and drain terminals of the second NMOS transistor,
 - wherein a gate of the second NMOS transistor is connected to the source and drain terminals of the first NMOS transistor,
 - wherein the first gate, the second pickup terminal, the gate of the first NMOS transistor and the source and drain terminals of the second NMOS transistor are connected to a first common terminal, and
 - wherein the second gate, the first pickup terminal, the gate of the second NMOS transistor and the source and drain terminals of the first NMOS transistor are connected to a second common terminal.

8. (cancelled)

9. (cancelled)

10. (cancelled)